

	Type	L #	Hits	S arch Text	DBs	Tim Stamp
1	BRS	L1	28539	(electrical\$6 near2 (test\$6 or exam\$6 or check\$6))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 18:05
2	BRS	L2	56042	"flash memory"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 18:07
3	BRS	L3	152370	"breakdown voltage" or "threshold voltage" or "state charge" or "interface charge" or "trapped charge" or "surface charge" or "programming cycle" or "erase cycle time"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 18:07
4	BRS	L4	101697 3	"flash memory" or IC or "integrated circuit" or microprocessor	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 18:08
5	BRS	L5	215537	parameter near8 (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 18:09

	Type	L #	Hits	Search Text	DBs	Tim Stamp
6	BRS	L6	177	1 and 3 and 5 and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 18:18
7	BRS	L7	35	1 near8 3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 18:21
8	BRS	L8	109910 9	(deposit\$6 or form\$6 near8 ((gate near2 insulat\$6) or (gate near2 oxide)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 18:22
9	BRS	L9	22	7 and 8	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/01 18:23

	Typ	L #	Hits	S arch Text	DBs	Time Stamp
1	BRS	L6	118737 91	temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:17
2	BRS	L7	56042	"flash memory"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:17
3	BRS	L8	160833 6	(predetermined near2 (parameter or value)) same	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:21
4	BRS	L9	81794	gate near2 insulat\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:21
5	BRS	L10	149426 6	memory	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:21

	Typ	L #	Hits	S arch Text	DBs	Tim Stamp
6	BRS	L11	116	8 same 9	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:21
7	BRS	L12	8	11 and 7	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:22
8	BRS	L13	263	(deposit\$6 or form\$6 or creat\$6 or fabricat\$6) near8 9 near8 (predetermined near2 parameter or value)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:24
9	BRS	L14	22	13 and 7	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:27
10	BRS	L15	708298	premodel\$6 or pre-model\$6 or predetermin\$4 near8 6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:32

	Typ	L #	Hits	Search Text	DBs	Tim Stamp
11	BRS	L16	28539	(electrical\$6 near2 (test\$6 or exam\$6 or check\$6))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:32
12	BRS	L17	152370	"breakdown voltage" or "threshold voltage" or "state charge" or "interface charge" or "trapped charge" or "surface charge" or "programming cycle" or "erase cycle time"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:33
13	BRS	L18	4	15 same 16 same 17	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:35
14	BRS	L19	420	15 same 9	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:36
15	BRS	L20	225	19 same (deposit\$6 or fabricat\$6 or form\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:56

	Typ	L #	Hits	S arch Text	DBs	Tim Stamp
16	BRS	L21	28539	((electrical\$6 near2 (test\$6 or exam\$6 or check\$6)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:57
17	BRS	L22	0	20 and 21	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:57
18	BRS	L23	222286 6	test\$6 or exam\$6 or check\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:58
19	BRS	L24	37	20 and 23	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/02 15:59

	Typ	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L3	1018778	"flash memory" or IC or "integrated circuit" or microprocessor	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:53
2	BRS	L4	215839	parameter near8 (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:54
3	BRS	L7	1100563	(deposit\$6 or form\$6 near8 ((gate near2 insulat\$6) or (gate near2 oxide)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:55
4	BRS	L10	11887502	temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:55
5	BRS	L11	56279	"flash memory"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:55

	Type	L #	Hits	Search T xt	DBs	Time Stamp
6	BRS	L12	161010	(predetermined near2 (parameter or value)) same (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:56
7	BRS	L13	82005	gate near2 insulat\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:56
8	BRS	L14	149672 4	memory	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:56
9	BRS	L15	116	((predetermined near2 (parameter or value)) same (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)) same (gate near2 insulat\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:56
10	BRS	L17	263	(deposit\$6 or form\$6 or creat\$6 or fabricat\$6) near8 (gate near2 insulat\$4) near8 (predetermined near2 parameter or value)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:32



	Typ	L #	Hits	S arch T xt	DBs	Tim Stamp
11	BRS	L19	709141	premodel\$6 or pre-model\$6 or predetermin\$4 near8 (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:56
12	BRS	L20	28591	(electrical\$6 near2 (test\$6 or exam\$6 or check\$6))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:57
13	BRS	L21	152568	"breakdown voltage" or "threshold voltage" or "state charge" or "interface charge" or "trapped charge" or "surface charge" or "programming cycle" or "erase cycle time"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:57
14	BRS	L23	420	(premodel\$6 or pre-model\$6 or predetermin\$4 near8 (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)) same (gate near2 insulat\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:57
15	BRS	L25	28591	((electrical\$6 near2 (test\$6 or exam\$6 or check\$6)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:57

	Type	L #	Hits	S arch Text	DBs	Time Stamp
16	BRS	L26	0	((premodel\$6 or pre-model\$6 or predetermin\$4 near8 (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)) same (gate near2 insulat\$4)) same (deposit\$6 or fabricat\$6 or form\$6)) and (((electrical\$6 near2 (test\$6 or exam\$6 or check\$6))))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:57
17	BRS	L27	222558 9	test\$6 or exam\$6 or check\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:57
18	BRS	L29	286	(test\$6 or check\$6 or exam\$6) with (gate adj insulat\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58
19	IS&R	L31	1479	(438/14).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58

	Typ	L #	Hits	S arch Text	DBs	Tim Stamp
20	BRS	L5	177	((electrical\$6 near2 (test\$6 or exam\$6 or check\$6)) ) and ("breakdown voltage" or "threshold voltage" or "state charge" or "interface charge" or "trapped charge" or "surface charge" or "programming cycle" or "erase cycle time") and (parameter near8 (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)) and ("flash memory" or IC or "integrated circuit" or microprocessor)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58
21	BRS	L6	35	((electrical\$6 near2 (test\$6 or exam\$6 or check\$6)) ) near8 ("breakdown voltage" or "threshold voltage" or "state charge" or "interface charge" or "trapped charge" or "surface charge" or "programming cycle" or "erase cycle time")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58
22	BRS	L8	22	((electrical\$6 near2 (test\$6 or exam\$6 or check\$6)) ) near8 ("breakdown voltage" or "threshold voltage" or "state charge" or "interface charge" or "trapped charge" or "surface charge" or "programming cycle" or "erase cycle time")) and ((deposit\$6 or form\$6 near8 ((gate near2 insulat\$6) or (gate near2 oxide))))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58

	Typ	L #	Hits	S arch T xt	DBs	Time Stamp
23	IS&R	L9	2	("5798534").PN.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58
24	BRS	L16	8	((predetermined near2 (parameter or value)) same (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)) same (gate near2 insulat\$4)) and "flash memory"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58
25	BRS	L18	22	((deposit\$6 or form\$6 or creat\$6 or fabricat\$6) near8 (gate near2 insulat\$4) near8 (predetermined near2 parameter or value)) and "flash memory"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58
26	BRS	L22	4	(premodel\$6 or pre-model\$6 or predetermin\$4 near8 (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)) same ((electrical\$6 near2 (test\$6 or exam\$6 or check\$6)) ) same ("breakdown voltage" or "threshold voltage" or "state charge" or "interface charge" or "trapped charge" or "surface charge" or "programming cycle" or "erase cycle time")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58

	Type	L #	Hits	Search T xt	DBs	Tim Stamp
27	BRS	L24	225	((premodel\$6 or pre-model\$6 or predetermin\$4 near8 (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)) same (gate near2 insulat\$4)) same (deposit\$6 or fabricat\$6 or form\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58
28	BRS	L28	37	((premodel\$6 or pre-model\$6 or predetermin\$4 near8 (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)) same (gate near2 insulat\$4)) same (deposit\$6 or fabricat\$6 or form\$6)) and (test\$6 or exam\$6 or check\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58
29	BRS	L30	121	((test\$6 or check\$6 or exam\$6) with (gate adj insulat\$6)) same (temperature or pressure or duration or time or gas or "flow rate" or composition or "liquid flow rate" or "liquid composition" or power)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 09:58
30	BRS	L32	10	((438/14).CCLS.) and (DRAM or "dynamic random access memory") and parametric and (test or testing)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:23

	Type	L #	Hits	S arch Text	DBs	Tim Stamp
31	BRS	L33	537	(DRAM or "dynamic random access memory") and parametric and (test or testing)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:15
32	BRS	L34	9	33 and 13	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:23
33	BRS	L35	0	32 and 17	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:23
34	BRS	L36	1479	((438/14).CCLS.)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:23
35	BRS	L37	1	36 and 17	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:23

	Typ	L #	Hits	Search Text	DBs	Time Stamp
36	BRS	L38	15	17 and 29	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:29
37	BRS	L39	141051 3	test or testing	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:29
38	BRS	L40	45351	39 and (chip or chips or dice or dies or IC or "integrated circuit" or DRAM or dynamic or memory) and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:31
39	BRS	L41	5653	40 and 12	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:31
40	BRS	L42	5653	41 and 10	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:32

	Type	L #	Hits	S arch Text	DBs	Tim Stamp
41	BRS	L43	46928	(deposit\$6 or form\$6 or creat\$6 or fabricat\$6) near8 (gate near2 insulat\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:35
42	BRS	L44	12896	43 and 21	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:35
43	BRS	L45	0	44 and 26	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:35
44	BRS	L46	45	44 and parametric	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:40
45	BRS	L47	0	(creat\$6 or form or forming or fabricat\$6) near4 (gate adj insulat\$6) near8 (used or using or use) near8 (predetermined near2 (test or testing or result or value or parameter or parametric))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 10:41



	Type	L #	Hits	Search Text	DBs	Time Stamp
46	BRS	L48	21	(creat\$6 or form or forming or fabricat\$6) same (gate adj insulat\$6) same (used or using or use) same (predetermined near2 (test or testing or result or value or parameter or parametric))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 11:38
47	BRS	L49	206	(test or testing or check or checking) near8 (gate near2 insulat\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/07/06 11:39